

Amendments to the Specification

Please replace the paragraph beginning on page 9, line 17, with the following rewritten paragraph:

The data lines 6a are electrically connected through contact holes 5 to source regions of semiconductor layers 1a of monocrystalline silicon described below. The pixel electrodes 9a are electrically connected through contact holes 8 to drain regions of the semiconductor layers 1a described below. The scanning lines 3a are disposed so as to oppose channel regions of the semiconductor layers 1a. The scanning lines 3a function as gate electrodes. Thus, the scanning line includes main portions and gate electrodes 3.

Please replace the paragraph beginning on page 10, line 8, with the following rewritten paragraph:

Fig. 3 is an expanded plan view of the TFT shown in Fig. 2. In Fig. 3, the gate-length direction is a direction in which the data line 6a extends longitudinally/lengthwise, and the gate-width direction is a direction perpendicular to the gate-length direction. Each semiconductor layer 1a is electrically separated completely from the other semiconductor layers by a mesa-etching method, LOCOS method, or the like. The gate electrode 3 is provided on the semiconductor layer 1a through an insulating film. At least one portion of the ends ~~in the gate width direction~~ of each gate electrode 3 is disposed on the semiconductor layer 1a, which does not extend toward the outside of the semiconductor layer 1a, at least in an intersection between the data line 6a and the scanning line 3a where the data line 6a crosses the scanning line 3a, and is disposed within the data line 6a, as in a conventional TFT. ~~The At least one portion of the ends in the gate length direction~~ of the gate electrode 3 ~~extend toward the~~ outside of the channel region of the semiconductor layer 1a. layer 1a, outside of the semiconductor layer 1a and outside of the data line 6a. A contact hole 7 for

connection to the capacitance line 3b is provided on at least one of the ends of the semiconductor layer 1a extending toward the outside of the gate electrode 3.